## BC856B, BC857B, BC858A

## General Purpose Transistors

## PNP Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 which is designed for low power surface mount applications.

## Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| Rating |  | Symbol | Value | Unit |
| :--- | :--- | :---: | :---: | :---: |
| Collector-Emitter Voltage |  | $\mathrm{V}_{\text {CEO }}$ |  | V |
|  | $\mathrm{BC856}$ |  | -65 |  |
|  | $\mathrm{BC857}$ |  | -45 |  |
|  | $\mathrm{BC858}$ |  | -30 |  |
| Collector-Base Voltage |  | $\mathrm{V}_{\text {CBO }}$ |  | V |
|  | $\mathrm{BC856}$ |  | -80 |  |
|  | BC857 |  | -50 |  |
|  | $\mathrm{BC858}$ |  | -30 |  |
| Emitter-Base Voltage |  | $\mathrm{V}_{\text {EBO }}$ | -5.0 | V |
| Collector Current - Continuous | $\mathrm{I}_{\mathrm{C}}$ | -100 | mAdc |  |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
| :---: | :---: | :---: | :---: |
| Total Device Dissipation FR-5 Board, <br> (Note 1) $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | 150 | mW |
| Thermal Resistance, <br> Junction-to-Ambient | $\mathrm{R}_{\theta \mathrm{JA}}$ | 883 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction and Storage Temperature | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $F R-5=1.0 \times 0.75 \times 0.062 \mathrm{in}$.

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SC-70/SOT-323 CASE 419 STYLE 3

## MARKING DIAGRAM



XX = Specific Device Code
M = Date Code*

- = Pb-Free Package
(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION
See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS $\left(T_{A}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Characteristic |  | Symbol | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |  |  |
| Collector-Emitter Breakdown Voltage $\left(\mathrm{I}_{\mathrm{C}}=-10 \mathrm{~mA}\right)$ | $\begin{aligned} & \text { BC856 } \\ & \text { BC857 } \\ & \text { BC858 } \end{aligned}$ | $\mathrm{V}_{\text {(BR)CEO }}$ | $\begin{aligned} & \hline-65 \\ & -45 \\ & -30 \end{aligned}$ | - | - | V |
| Collector-Emitter Breakdown Voltage $\left(\mathrm{I}_{\mathrm{C}}=-10 \mu \mathrm{~A}, \mathrm{~V}_{\mathrm{EB}}=0\right)$ | BC856 BC857 BC858 | $\mathrm{V}_{\text {(BR) }}$ CES | $\begin{aligned} & \hline-80 \\ & -50 \\ & -30 \end{aligned}$ | - | - | V |
| Collector-Base Breakdown Voltage $\left(\mathrm{I}_{\mathrm{C}}=-10 \mu \mathrm{~A}\right)$ | BC856 BC857 BC858 | $\mathrm{V}_{(\mathrm{BR}) \mathrm{CBO}}$ | $\begin{aligned} & \hline-80 \\ & -50 \\ & -30 \end{aligned}$ | - | - | V |
| $\begin{aligned} & \text { Emitter-Base Breakdown Voltage } \\ & \left(I_{E}=-1.0 \mu \mathrm{~A}\right) \end{aligned}$ | $\begin{aligned} & \text { BC856 } \\ & \text { BC857 } \\ & \text { BC858 } \end{aligned}$ | $\mathrm{V}_{(\mathrm{BR}) \text { EBO }}$ | $\begin{aligned} & \hline-5.0 \\ & -5.0 \\ & -5.0 \end{aligned}$ | - | - | V |
| $\begin{aligned} \text { Collector Cutoff Current } \begin{aligned} \left(\mathrm{V}_{\mathrm{CB}}\right. & =-30 \mathrm{~V}) \\ \left(\mathrm{V}_{\mathrm{CB}}\right. & \left.=-30 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=150^{\circ} \mathrm{C}\right) \end{aligned} \end{aligned}$ |  | $\mathrm{I}_{\text {cbo }}$ | - | - | $\begin{aligned} & \hline-15 \\ & -4.0 \end{aligned}$ | $\begin{aligned} & \mathrm{nA} \\ & \mu \mathrm{~A} \end{aligned}$ |

ON CHARACTERISTICS

| DC Current Gain BC856A, BC585A <br> $\left(\mathrm{I}_{\mathrm{C}}=-10 \mu \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=-5.0 \mathrm{~V}\right)$ BC856B, BC857B, BC858B <br>  BC857C <br> $\left(\mathrm{I}_{\mathrm{C}}=-2.0 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-5.0 \mathrm{~V}\right)$  <br>  BC856A, BC858A <br>  BC856B, BC857B, BC858B <br>  BC857C | $h_{\text {FE }}$ | $\begin{aligned} & 125 \\ & 220 \\ & 420 \end{aligned}$ | $\begin{gathered} \hline 90 \\ 150 \\ 270 \\ \\ 180 \\ 290 \\ 520 \end{gathered}$ | $\begin{gathered} \hline- \\ - \\ - \\ 250 \\ 475 \\ 800 \end{gathered}$ | - |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\begin{aligned} & \text { Collector-Emitter Saturation Voltage } \\ & \left(I_{C}=-10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=-0.5 \mathrm{~mA}\right) \\ & \left(\mathrm{I}_{\mathrm{C}}=-100 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=-5.0 \mathrm{~mA}\right) \end{aligned}$ | $\mathrm{V}_{\text {CE(sat) }}$ |  |  | $\begin{gathered} -0.3 \\ -0.65 \end{gathered}$ | V |
| Base-Emitter Saturation Voltage $\begin{aligned} & \left(I_{C}=-10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=-0.5 \mathrm{~mA}\right) \\ & \left(\mathrm{I}_{\mathrm{C}}=-100 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=-5.0 \mathrm{~mA}\right) \end{aligned}$ | $\mathrm{V}_{\mathrm{BE} \text { (sat) }}$ |  | $\begin{aligned} & -0.7 \\ & -0.9 \end{aligned}$ | - | V |
| $\begin{aligned} & \text { Base-Emitter On Voltage } \\ & \left(\mathrm{I}_{\mathrm{C}}=-2.0 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-5.0 \mathrm{~V}\right) \\ & \left(\mathrm{I}_{\mathrm{C}}=-10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-5.0 \mathrm{~V}\right) \end{aligned}$ | $\mathrm{V}_{\mathrm{BE} \text { (on) }}$ | -0.6 | - | $\begin{aligned} & -0.75 \\ & -0.82 \end{aligned}$ | V |

SMALL-SIGNAL CHARACTERISTICS

| Current-Gain - Bandwidth Product <br> $\left(\mathrm{IC}_{\mathrm{C}}=-10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-5.0 \mathrm{Vdc}, \mathrm{f}=100 \mathrm{MHz}\right)$ | $\mathrm{f}_{\mathrm{T}}$ | 100 | - | - | MHz |
| :--- | :---: | :---: | :---: | :---: | :---: |
| Output Capacitance <br> $\left(\mathrm{V}_{\mathrm{CB}}=-10 \mathrm{~V}, \mathrm{f}=1.0 \mathrm{MHz}\right)$ | $\mathrm{C}_{\mathrm{ob}}$ | - | - | 4.5 | pF |
| Noise Figure <br> $\left(\mathrm{I}_{\mathrm{C}}=-0.2 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-5.0 \mathrm{Vdc}, \mathrm{R}_{\mathrm{S}}=2.0 \mathrm{k} \Omega\right.$, <br> $\mathrm{f}=1.0 \mathrm{kHz}, \mathrm{BW}=200 \mathrm{~Hz})$ | NF | - | - | 10 | dB |

> BC856B, BC857B, BC858A

## BC857/BC858



Figure 1. Normalized DC Current Gain


Figure 3. Collector Saturation Region


Figure 5. Capacitances


Figure 2. "Saturation" and "On" Voltages


Figure 4. Base-Emitter Temperature Coefficient


Figure 6. Current-Gain - Bandwidth Product

## BC856B, BC857B, BC858A



Figure 7. DC Current Gain


Figure 9. Collector Saturation Region


Figure 11. Capacitance


Figure 8. "On" Voltage


Figure 10. Base-Emitter Temperature Coefficient


Figure 12. Current-Gain - Bandwidth Product


Figure 13. Thermal Response


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate $\mathrm{I}_{\mathrm{C}}-\mathrm{V}_{\mathrm{CE}}$ limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $\mathrm{T}_{\mathrm{J}(\mathrm{pk})}=150^{\circ} \mathrm{C} ; \mathrm{T}_{\mathrm{C}}$ or $\mathrm{T}_{\mathrm{A}}$ is variable depending upon conditions. Pulse curves are valid for duty cycles to $10 \%$ provided $\mathrm{T}_{\mathrm{J}(\mathrm{pk})} \leq 150^{\circ} \mathrm{C}$. $\mathrm{T}_{\mathrm{J}(\mathrm{pk})}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

## ORDERING INFORMATION

| Device | Marking | Package | Shipping ${ }^{\dagger}$ |
| :--- | :---: | :---: | :---: |
| BC856BWT1G | $3 B$ | $\begin{array}{c}\text { SC-70/SOT-323 } \\ \text { (Pb-Free) }\end{array}$ |  |
| SBC856BWT1G* | $3 F$ | $\begin{array}{c}\text { SC-70/SOT-323 } \\ \text { (Pb-Free) }\end{array}$ | $3,000 /$ Tape \& Reel |$]$| $3,000 /$ Tape \& Reel |
| :--- |

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## SC-70 (SOT-323)

CASE 419-04
ISSUE N
DATE 11 NOV 2008

SCALE 4:1


SOLDERING FOOTPRINT*


SCALE 10:1 $\left(\frac{\mathrm{mm}}{\text { inches }}\right)$

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

|  | MILLIMETERS |  |  | INCHES |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| DIM | MIN | NOM | MAX | MIN | NOMM | MAX |  |
| A | 0.80 | 0.90 | 1.00 | 0.032 | 0.035 | 0.040 |  |
| A1 | 0.00 | 0.05 | 0.10 | 0.000 | 0.002 | 0.004 |  |
| A2 | 0.70 REF |  |  | 0.028 REF |  |  |  |
| b | 0.30 | 0.35 | 0.40 | 0.012 | 0.014 | 0.016 |  |
| c | 0.10 | 0.18 | 0.25 | 0.004 | 0.007 | 0.010 |  |
| D | 1.80 | 2.10 | 2.20 | 0.071 | 0.083 | 0.087 |  |
| E | 1.15 | 1.24 | 1.35 | 0.045 | 0.049 | 0.053 |  |
| e | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |  |
| e1 | 0.65 BSC |  |  |  | 0.026 BSC |  |  |
| L | 0.20 | 0.38 | 0.56 | 0.008 | 0.015 | 0.022 |  |
| HE $^{2}$ | 2.00 | 2.10 | 2.40 | 0.079 | 0.083 | 0.095 |  |

## GENERIC MARKING DIAGRAM

*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " $\quad$ ", may or may not be present.


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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | SC-70 (SOT-323) | PAGE 1 OF 1 |

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## PUBLICATION ORDERING INFORMATION

## LITERATURE FULFILLMENT

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[^0]:    $\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
    *S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

